

### IN THE CLAIMS

Please cancel claims 7-33 without prejudice.

Please amend the following claims. Please add new claims 34-39.

1. (Previously Presented) A method of rinsing a wafer comprising:  
spinning a wafer;  
exposing said spinning wafer to DI water while providing sonic waves to substantially the entire surface area of the wafer; and  
after exposing said spinning wafer to DI water, exposing said spinning wafer to a liquid or vapor having a lower surface tension than water.
2. (Previously Presented) The method of claim 1 wherein said liquid is or vapor comprises isopropyl alcohol (IPA).
3. (Previously Presented) The method of claim 1 wherein said sonic waves are applied to the backside of said wafer.
4. (Original) The method of claim 1 further comprising the step of heating said DI water to a temperature greater than room temperature prior to exposing said spinning wafer to said DI water.
5. (Previously Presented) The method of claim 1 wherein said wafer is spun at a rate between 50-1000 rpms while exposing said wafer to said DI water and to said liquid or vapor.

6. (Previously Presented) The method of claim 2 wherein the time of exposure to said liquid is less than time of exposure to said DI water or vapor.

7-33. (Canceled)

34. (New) A method of rinsing a wafer comprising:  
spinning a wafer;  
exposing said spinning wafer to water while providing sonic waves to substantially the entire surface area of the wafer; and  
after exposing said spinning wafer to water, exposing said spinning wafer to a liquid or vapor having a lower surface tension than water.

35. (New) The method of claim 34 wherein said liquid is or vapor comprises isopropyl alcohol (IPA).

36. (New) The method of claim 34 wherein said sonic waves are applied to the backside of said wafer.

37. (New) The method of claim 34 further comprising the step of heating said DI water to a temperature greater than room temperature prior to exposing said spinning wafer to said water.

38. (New) The method of claim 34 wherein said wafer is spun at a rate between 50-1000 rpms while exposing said wafer to said water and to said liquid or vapor.

39. (New) The method of claim 35 wherein the time of exposure to said liquid is less than time of exposure to said water or vapor.